

Transistors

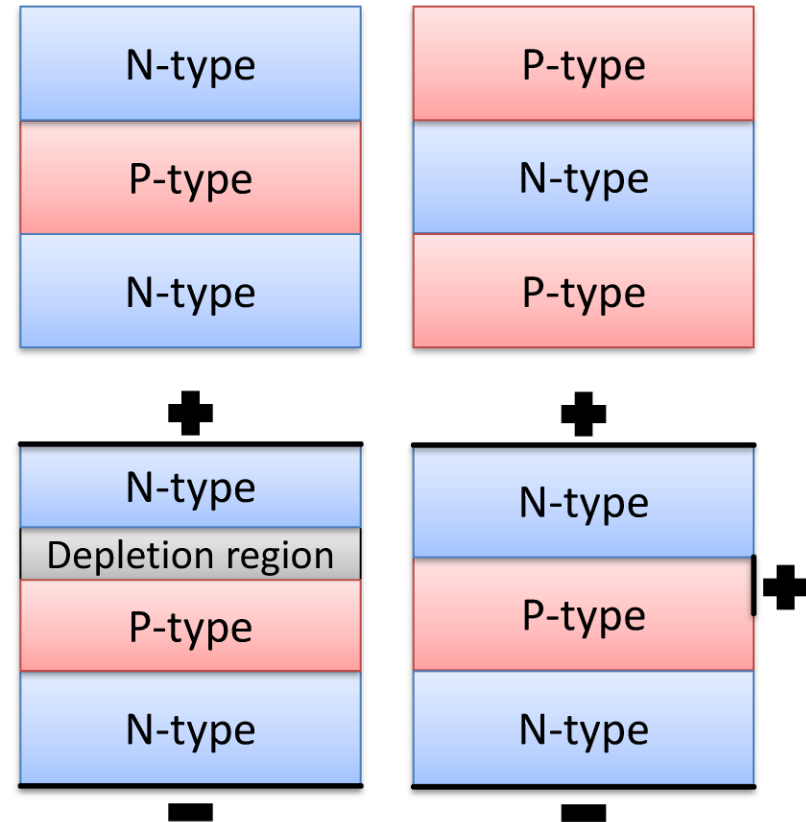
Networks and Embedded Software

Module 3.1.2

by Wolfgang Neff

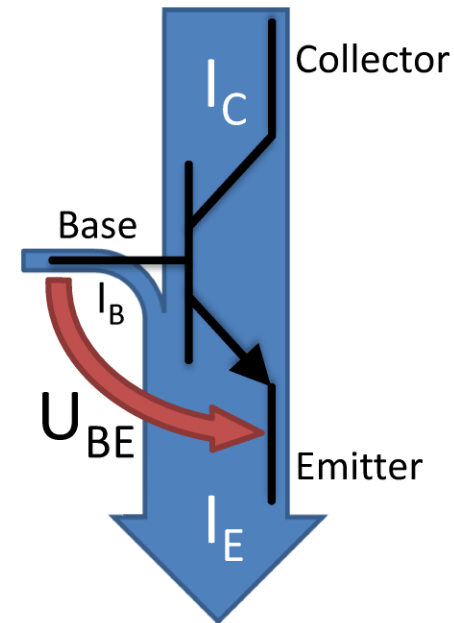
Transistors

- Structure
 - Bipolar junction transistor (BJT)
 - Two p-n junctions
 - NPN transistor
 - PNP transistor
 - Third connection
 - Insulator
 - Conductor



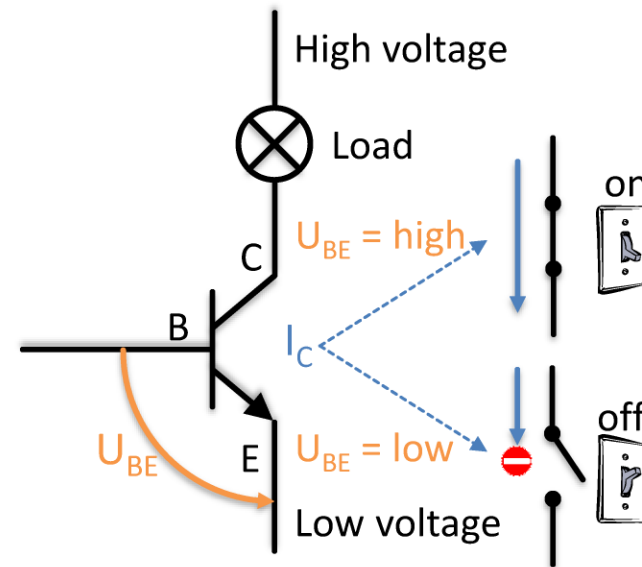
NPN Transistors (1)

- Characteristics
 - Collector current flows if base current flows
 - Base current flows into base
 - Positive voltage drop between base and emitter necessary



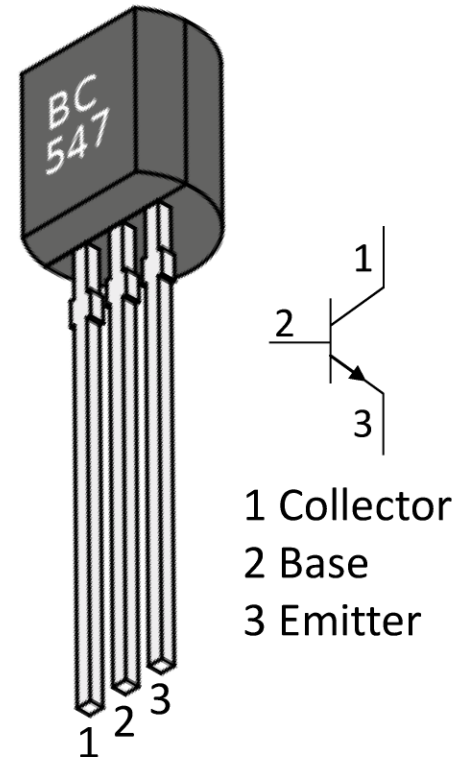
NPN Transistors (2)

- Application: switch
 - Load in collector branch
 - Controlled by base
 - Switch is
 - On if U_{BE} is positive
 - Off if U_{BE} is zero
 - Active high
 - On if U_{BE} is high
 - Off if U_{BE} is low



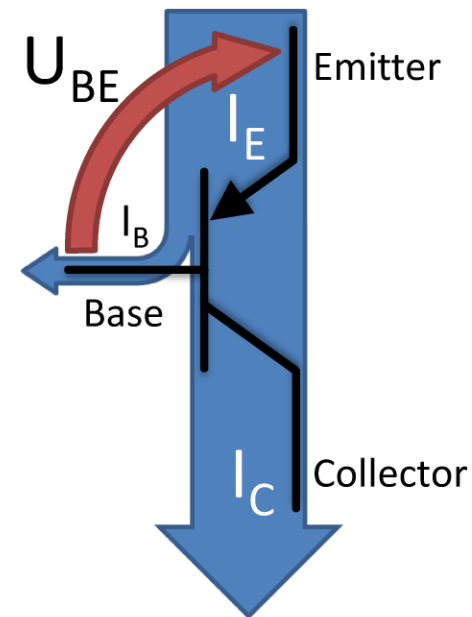
NPN Transistors (3)

- Example: BC547
 - Maximum collector current
 - $I_C = 100 \text{ mA}$
 - Base saturation voltage
 - $U_{BE} = 0.7 \text{ V}$
 - DC current gain
 - $h_{FE} = \frac{I_C}{I_B}$
 - $h_{FE} \approx 250$



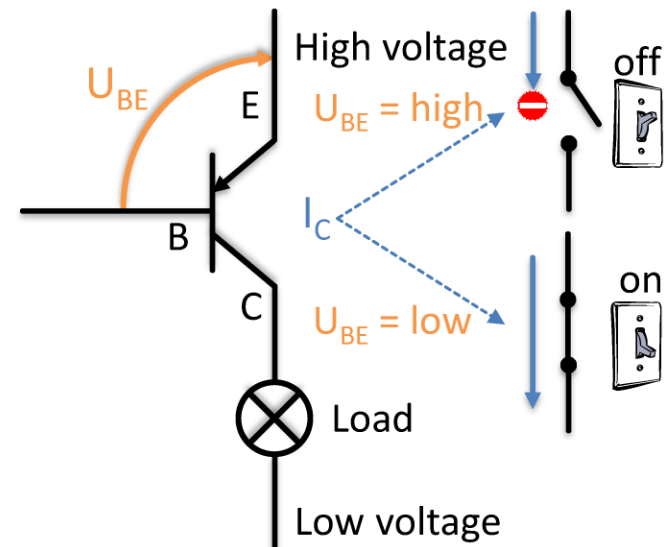
PNP Transistors (1)

- Characteristics
 - Collector current flows if base current flows
 - Base current flows out of base
 - Negative voltage drop between base and emitter necessary



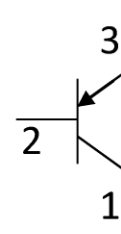
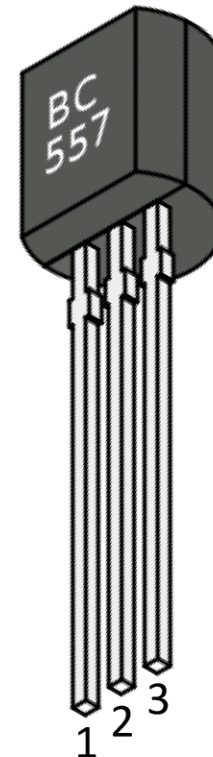
PNP Transistors (2)

- Application: switch
 - Load in collector branch
 - Controlled by base
 - Switch is
 - On if U_{BE} is negative
 - Off if U_{BE} is zero
 - Active low
 - On if U_{BE} is low
 - Off if U_{BE} is high



PNP Transistors (3)

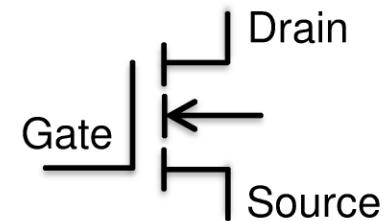
- Example: BC557
 - Maximum collector current
 - $I_C = -100 \text{ mA}$
 - Base saturation voltage
 - $U_{BE} = -0.7 \text{ V}$
 - DC current gain
 - $h_{FE} = \frac{I_C}{I_B}$
 - $h_{FE} \approx 250$



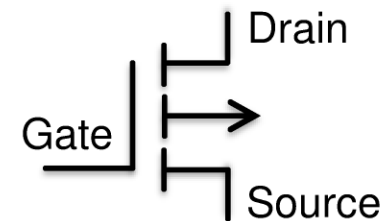
1 Collector
2 Base
3 Emitter

MOSFET (1)

- Metal-Oxide-Semiconductor
 - Composition
- Field-Effect Transistor
 - Operating mode
 - Controlled by voltage
 - No current necessary
 - Energy efficient



N-channel, enhancement mode



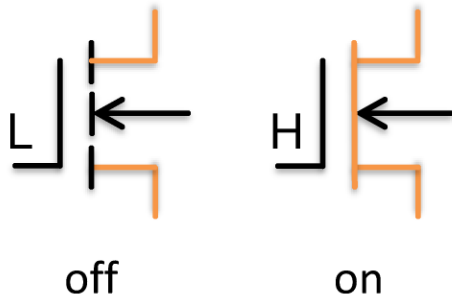
P-channel, enhancement mode

MOSFET (2)

- Application: switch

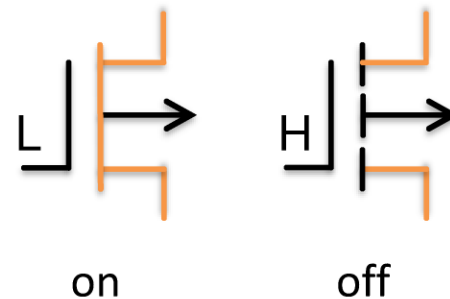
- N-Channel

- Drain current
 - On if gate high
 - Off if gate low
- Active high



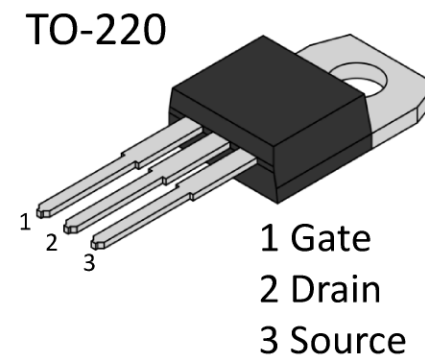
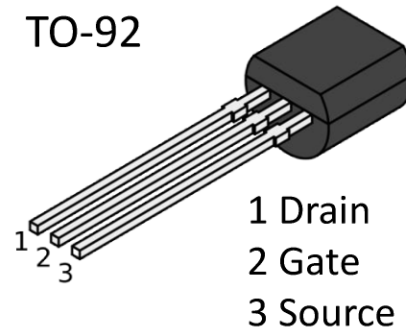
- P-Channel

- Drain current
 - On if gate low
 - Off if gate high
- Active low



MOSFET (3)

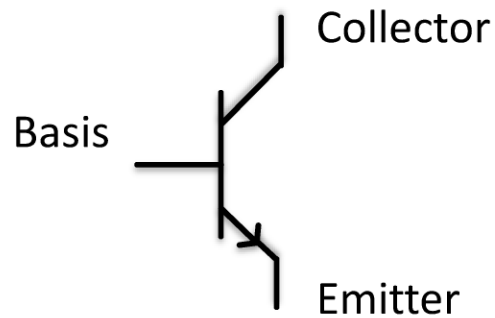
- Examples
 - 2N7000
 - N-Channel MOSFET
 - Max drain current $I_D = 0.2 \text{ A}$
 - BS250
 - P-Channel MOSFET
 - IRF510
 - N-Channel Power MOSFET
 - Max drain current $I_D = 5.6 \text{ A}$



MOSFET (4)

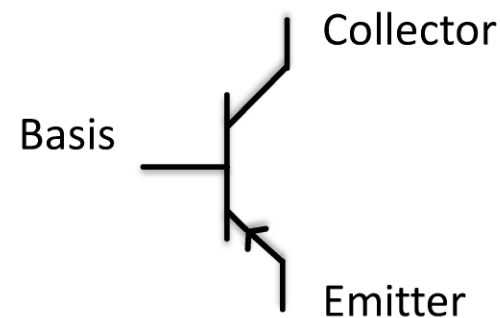
- Comparison

- NPN / N-Channel



BJT

- PNP / P-Channel



MOSFET

